

Ting-Chang Chang

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

486 papers	7,886 citations	40 h-index	66 g-index
516 ext. papers	8,852 ext. citations	3.6 avg, IF	5.82 L-index

#	Paper	IF	Citations
486	Resistance random access memory. <i>Materials Today</i> , 2016 , 19, 254-264	21.8	282
485	Developments in nanocrystal memory. <i>Materials Today</i> , 2011 , 14, 608-615	21.8	267
484	Influence of electrode material on the resistive memory switching property of indium gallium zinc oxide thin films. <i>Applied Physics Letters</i> , 2010 , 96, 262110	3.4	177
483	Behaviors of InGaZnO thin film transistor under illuminated positive gate-bias stress. <i>Applied Physics Letters</i> , 2010 , 97, 112104	3.4	150
482	Influence of positive bias stress on N2O plasma improved InGaZnO thin film transistor. <i>Applied Physics Letters</i> , 2010 , 96, 242105	3.4	147
481	Multilevel resistive switching in Ti/CuxO/Pt memory devices. <i>Journal of Applied Physics</i> , 2010 , 108, 1141105	10.5	129
480	Investigating the degradation behavior caused by charge trapping effect under DC and AC gate-bias stress for InGaZnO thin film transistor. <i>Applied Physics Letters</i> , 2011 , 99, 022104	3.4	120
479	Redox Reaction Switching Mechanism in RRAM Device With $\text{Pt/CoSiO}_2/\text{TiN}$ Structure. <i>IEEE Electron Device Letters</i> , 2011 , 32, 545-547	4.4	117
478	Bias-induced oxygen adsorption in zinc tin oxide thin film transistors under dynamic stress. <i>Applied Physics Letters</i> , 2010 , 96, 262104	3.4	111
477	Physical and chemical mechanisms in oxide-based resistance random access memory. <i>Nanoscale Research Letters</i> , 2015 , 10, 120	5	109
476	Bipolar Resistive Switching Characteristics of Transparent Indium Gallium Zinc Oxide Resistive Random Access Memory. <i>Electrochemical and Solid-State Letters</i> , 2010 , 13, H191		93
475	Light-induced instability of an InGaZnO thin film transistor with and without SiOx passivation layer formed by plasma-enhanced-chemical-vapor-deposition. <i>Applied Physics Letters</i> , 2010 , 97, 192103	3.4	90
474	Atomic-level quantized reaction of HfOx memristor. <i>Applied Physics Letters</i> , 2013 , 102, 172903	3.4	88
473	Integrated one diode-one resistor architecture in nanopillar SiOx resistive switching memory by nanosphere lithography. <i>Nano Letters</i> , 2014 , 14, 813-8	11.5	85
472	Demonstration of Synaptic Behaviors and Resistive Switching Characterizations by Proton Exchange Reactions in Silicon Oxide. <i>Scientific Reports</i> , 2016 , 6, 21268	4.9	73
471	Environment-dependent thermal instability of sol-gel derived amorphous indium-gallium-zinc-oxide thin film transistors. <i>Applied Physics Letters</i> , 2011 , 98, 152109	3.4	70
470	A low-temperature method for improving the performance of sputter-deposited ZnO thin-film transistors with supercritical fluid. <i>Applied Physics Letters</i> , 2009 , 94, 162111	3.4	69

469	High-Performance Visible-Blind Ultraviolet Photodetector Based on IGZO TFT Coupled with p-n Heterojunction. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 8102-8109	9.5	67
468	Effects of Ambient Atmosphere on Electrical Characteristics of Al ₂ O ₃ Passivated InGaZnO Thin Film Transistors during Positive-Bias-Temperature-Stress Operation. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H177		65
467	Influence of H ₂ O Dipole on Subthreshold Swing of Amorphous Indium Gallium Zinc-Oxide Thin Film Transistors. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H114		60
466	Enhancing the Oxygen Plasma Resistance of Low-k Methylsilsesquioxane by H ₂ Plasma Treatment. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, 3482-3486	1.4	60
465	Functionally Complete Boolean Logic in 1T1R Resistive Random Access Memory. <i>IEEE Electron Device Letters</i> , 2017 , 38, 179-182	4.4	57
464	Characteristics and Mechanisms of Silicon-Oxide-Based Resistance Random Access Memory. <i>IEEE Electron Device Letters</i> , 2013 , 34, 399-401	4.4	56
463	Origin of Hopping Conduction in Graphene-Oxide-Doped Silicon Oxide Resistance Random Access Memory Devices. <i>IEEE Electron Device Letters</i> , 2013 , 34, 677-679	4.4	53
462	Low-power bipolar resistive switching TiN/HfO ₂ /ITO memory with self-compliance current phenomenon. <i>Applied Physics Express</i> , 2014 , 7, 034101	2.4	52
461	Reducing operation current of Ni-doped silicon oxide resistance random access memory by supercritical CO ₂ fluid treatment. <i>Applied Physics Letters</i> , 2011 , 99, 263501	3.4	50
460	Charge Quantity Influence on Resistance Switching Characteristic During Forming Process. <i>IEEE Electron Device Letters</i> , 2013 , 34, 502-504	4.4	49
459	Influence of Nanocrystals on Resistive Switching Characteristic in Binary Metal Oxides Memory Devices. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H135		49
458	A Novel Nanowire Channel Poly-Si TFT Functioning as Transistor and Nonvolatile SONOS Memory. <i>IEEE Electron Device Letters</i> , 2007 , 28, 809-811	4.4	49
457	A study of resistive switching effects on a thin FeOx transition layer produced at the oxide/iron interface of TiN/SiO ₂ /Fe-contented electrode structures. <i>Applied Physics Letters</i> , 2010 , 96, 052111	3.4	48
456	Characterization of Oxygen Accumulation in Indium-Tin-Oxide for Resistance Random Access Memory. <i>IEEE Electron Device Letters</i> , 2014 , 35, 630-632	4.4	47
455	Bipolar Resistive RAM Characteristics Induced by Nickel Incorporated Into Silicon Oxide Dielectrics for IC Applications. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1696-1698	4.4	47
454	Nonvolatile reconfigurable sequential logic in a HfO resistive random access memory array. <i>Nanoscale</i> , 2017 , 9, 6649-6657	7.7	45
453	Effects of H ₂ plasma treatment on low dielectric constant methylsilsesquioxane. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 2325		45
452	The Effect of Silicon Oxide Based RRAM with Tin Doping. <i>Electrochemical and Solid-State Letters</i> , 2012 , 15, H65		44

451	Origin of Hopping Conduction in Sn-Doped Silicon Oxide RRAM With Supercritical CO_2 Fluid Treatment. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1693-1695	4-4	43
450	Attaining resistive switching characteristics and selector properties by varying forming polarities in a single HfO ₂ -based RRAM device with a vanadium electrode. <i>Nanoscale</i> , 2017 , 9, 8586-8590	7-7	42
449	Realization of Functional Complete Stateful Boolean Logic in Memristive Crossbar. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 34559-34567	9-5	42
448	Bulk Oxygen Ion Storage in Indium Oxide Electrode for Improved Performance of HfO ₂ -Based Resistive Random Access Memory. <i>IEEE Electron Device Letters</i> , 2016 , 37, 280-283	4-4	41
447	Characteristics of hafnium oxide resistance random access memory with different setting compliance current. <i>Applied Physics Letters</i> , 2013 , 103, 163502	3-4	41
446	Complementary resistive switching behavior induced by varying forming current compliance in resistance random access memory. <i>Applied Physics Letters</i> , 2015 , 106, 213505	3-4	40
445	Investigating the Drain-Bias-Induced Degradation Behavior Under Light Illumination for InGaZnO Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1000-1002	4-4	40
444	Low operation voltage macromolecular composite memory assisted by graphene nanoflakes. <i>Journal of Materials Chemistry C</i> , 2013 , 1, 552-559	7-1	39
443	Performance and characteristics of double layer porous silicon oxide resistance random access memory. <i>Applied Physics Letters</i> , 2013 , 102, 253509	3-4	39
442	Dual Ion Effect of the Lithium Silicate Resistance Random Access Memory. <i>IEEE Electron Device Letters</i> , 2014 , 35, 530-532	4-4	38
441	Hopping effect of hydrogen-doped silicon oxide insert RRAM by supercritical CO ₂ fluid treatment. <i>IEEE Electron Device Letters</i> , 2013 , 34, 617-619	4-4	38
440	Review of Present Reliability Challenges in Amorphous In-Ga-Zn-O Thin Film Transistors. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, Q3058-Q3070	2	38
439	High-performance hydrogenated amorphous-Si TFT for AMLCD and AMOLED applications. <i>IEEE Electron Device Letters</i> , 2005 , 26, 731-733	4-4	38
438	Effect of mechanical-strain-induced defect generation on the performance of flexible amorphous InGaZnO thin-film transistors. <i>Applied Physics Express</i> , 2016 , 9, 124101	2-4	36
437	Electrical conduction mechanism of Zn:SiO ₂ resistance random access memory with supercritical CO ₂ fluid process. <i>Applied Physics Letters</i> , 2013 , 103, 083509	3-4	36
436	Enhancement of Brightness Uniformity by a New Voltage-Modulated Pixel Design for AMOLED Displays. <i>IEEE Electron Device Letters</i> , 2006 , 27, 743-745	4-4	36
435	Functional Demonstration of a Memristive Arithmetic Logic Unit (MemALU) for In-Memory Computing. <i>Advanced Functional Materials</i> , 2019 , 29, 1905660	15-6	35
434	Self-Heating-Effect-Induced Degradation Behaviors in a-InGaZnO Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2013 , 34, 63-65	4-4	35

433	Resistance Switching Induced by Hydrogen and Oxygen in Diamond-Like Carbon Memristor. <i>IEEE Electron Device Letters</i> , 2014 , 35, 1016-1018	4.4	35
432	Dehydroxyl effect of Sn-doped silicon oxide resistance random access memory with supercritical CO ₂ fluid treatment. <i>Applied Physics Letters</i> , 2012 , 101, 112906	3.4	35
431	Investigation for coexistence of dual resistive switching characteristics in DyMn ₂ O ₅ memory devices. <i>Applied Physics Letters</i> , 2011 , 99, 092106	3.4	35
430	Suppress temperature instability of InGaZnO thin film transistors by N ₂ O plasma treatment, including thermal-induced hole trapping phenomenon under gate bias stress. <i>Applied Physics Letters</i> , 2012 , 100, 182103	3.4	35
429	Reliability characteristics of NiSi nanocrystals embedded in oxide and nitride layers for nonvolatile memory application. <i>Applied Physics Letters</i> , 2008 , 92, 152114	3.4	35
428	Efficient Implementation of Boolean and Full-Adder Functions With 1T1R RRAMs for Beyond Von Neumann In-Memory Computing. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 4659-4666	2.9	35
427	Surface Engineering of Polycrystalline Silicon for Long-Term Mechanical Stress Endurance Enhancement in Flexible Low-Temperature Poly-Si Thin-Film Transistors. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 11942-11949	9.5	34
426	Effects of Repetitive Mechanical Bending Strain on Various Dimensions of Foldable Low Temperature Polysilicon TFTs Fabricated on Polyimide. <i>IEEE Electron Device Letters</i> , 2016 , 37, 1010-1013	4.4	34
425	An electro-photo-sensitive synaptic transistor for edge neuromorphic visual systems. <i>Nanoscale</i> , 2019 , 11, 17590-17599	7.7	34
424	Resistive switching characteristics of Sm ₂ O ₃ thin films for nonvolatile memory applications. <i>Solid-State Electronics</i> , 2011 , 63, 189-191	1.7	34
423	Low-temperature method for enhancing sputter-deposited HfO ₂ films with complete oxidization. <i>Applied Physics Letters</i> , 2007 , 91, 012109	3.4	34
422	Impact of repeated uniaxial mechanical strain on p-type flexible polycrystalline thin film transistors. <i>Applied Physics Letters</i> , 2015 , 106, 183503	3.4	33
421	Resistive Switching Modification by Ultraviolet Illumination in Transparent Electrode Resistive Random Access Memory. <i>IEEE Electron Device Letters</i> , 2014 , 35, 633-635	4.4	33
420	Endurance Improvement Technology With Nitrogen Implanted in the Interface of WSiO_x Resistance Switching Device. <i>IEEE Electron Device Letters</i> , 2013 , 34, 864-866	4.4	33
419	Silicon introduced effect on resistive switching characteristics of WOX thin films. <i>Applied Physics Letters</i> , 2012 , 100, 022904	3.4	33
418	LiSiOX-Based Analog Memristive Synapse for Neuromorphic Computing. <i>IEEE Electron Device Letters</i> , 2019 , 40, 542-545	4.4	33
417	NBTI Degradation in LTPS TFTs Under Mechanical Tensile Strain. <i>IEEE Electron Device Letters</i> , 2011 , 32, 907-909	4.4	32
416	Conduction Mechanism and Improved Endurance in HfO-Based RRAM with Nitridation Treatment. <i>Nanoscale Research Letters</i> , 2017 , 12, 574	5	31

4 ¹⁵	Hot carrier effect on gate-induced drain leakage current in high-k/metal gate n-channel metal-oxide-semiconductor field-effect transistors. <i>Applied Physics Letters</i> , 2011 , 99, 012106	3-4	3 ¹
4 ¹⁴	Improvement of resistance switching characteristics in a thin FeOx transition layer of TiN/SiO ₂ /FeOx/FePt structure by rapid annealing. <i>Applied Physics Letters</i> , 2010 , 96, 222108	3-4	3 ¹
4 ¹³	Reconfigurable Boolean Logic in Memristive Crossbar: The Principle and Implementation. <i>IEEE Electron Device Letters</i> , 2019 , 40, 200-203	4-4	3 ¹
4 ¹²	Resistive switching characteristics of gallium oxide for nonvolatile memory application. <i>Thin Solid Films</i> , 2013 , 529, 200-204	2-2	3 ⁰
4 ¹¹	Effects of Varied Negative Stop Voltages on Current Self-Compliance in Indium Tin Oxide Resistance Random Access Memory. <i>IEEE Electron Device Letters</i> , 2015 , 36, 564-566	4-4	3 ⁰
4 ¹⁰	Bipolar resistive switching of chromium oxide for resistive random access memory. <i>Solid-State Electronics</i> , 2011 , 62, 40-43	1-7	3 ⁰
4 ⁰⁹	Investigation statistics of bipolar multilevel memristive mechanism and characterizations in a thin FeOx transition layer of TiN/SiO ₂ /FeOx/Fe structure. <i>Journal of Applied Physics</i> , 2011 , 110, 053703	2-5	3 ⁰
4 ⁰⁸	Temperature and frequency dependence of the ferroelectric characteristics of BaTiO ₃ thin films for nonvolatile memory applications. <i>Applied Physics A: Materials Science and Processing</i> , 2007 , 89, 533-536	2-6	3 ⁰
4 ⁰⁷	Investigation of on-current degradation behavior induced by surface hydrolysis effect under negative gate bias stress in amorphous InGaZnO thin-film transistors. <i>Applied Physics Letters</i> , 2014 , 104, 103501	3-4	29
4 ⁰⁶	Self-heating enhanced charge trapping effect for InGaZnO thin film transistor. <i>Applied Physics Letters</i> , 2012 , 101, 042101	3-4	29
4 ⁰⁵	Improved memory window for Ge nanocrystals embedded in SiON layer. <i>Applied Physics Letters</i> , 2006 , 89, 162105	3-4	29
4 ⁰⁴	Galvanic Effect of Au/Ag Electrodes for Conductive Bridging Resistive Switching Memory. <i>IEEE Electron Device Letters</i> , 2015 , 36, 1321-1324	4-4	28
4 ⁰³	Asymmetric Carrier Conduction Mechanism by Tip Electric Field in WSiO_x Resistance Switching Device. <i>IEEE Electron Device Letters</i> , 2012 , 33, 342-344	4-4	28
4 ⁰²	A New Pixel Circuit Compensating for Brightness Variation in Large Size and High Resolution AMOLED Displays. <i>Journal of Display Technology</i> , 2007 , 3, 398-403		28
4 ⁰¹	Rational Hydrogenation for Enhanced Mobility and High Reliability on ZnO-based Thin Film Transistors: From Simulation to Experiment. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 5408-15	9-5	27
4 ⁰⁰	Low Temperature Improvement Method on ZnSiO_x Resistive Random Access Memory Devices. <i>IEEE Electron Device Letters</i> , 2013 , 34, 511-513	4-4	27
399	Influence of Bias-Induced Copper Diffusion on the Resistive Switching Characteristics of a SiON Thin Film. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H93		27
398	Flexible low-temperature polycrystalline silicon thin-film transistors. <i>Materials Today Advances</i> , 2020 , 5, 100040	7-4	26

397	Investigation of channel width-dependent threshold voltage variation in a-InGaZnO thin-film transistors. <i>Applied Physics Letters</i> , 2014 , 104, 133503	3.4	26
396	Ultra-violet light enhanced super critical fluid treatment in In-Ga-Zn-O thin film transistor. <i>Applied Physics Letters</i> , 2014 , 104, 243508	3.4	26
395	Origin of self-heating effect induced asymmetrical degradation behavior in InGaZnO thin-film transistors. <i>Applied Physics Letters</i> , 2012 , 100, 232101	3.4	26
394	Hydrogen induced redox mechanism in amorphous carbon resistive random access memory. <i>Nanoscale Research Letters</i> , 2014 , 9, 52	5	25
393	Temperature-Dependent Instability of Bias Stress in InGaZnO Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 2119-2124	2.9	25
392	Hot-Carrier Effect on Amorphous In-Ga-Zn-O Thin-Film Transistors With a Via-Contact Structure. <i>IEEE Electron Device Letters</i> , 2013 , 34, 638-640	4.4	25
391	High-performance polycrystalline silicon thin-film transistor with multiple nanowire channels and lightly doped drain structure. <i>Applied Physics Letters</i> , 2004 , 84, 3822-3824	3.4	25
390	Improvement of Resistive Switching Characteristic in Silicon Oxide-Based RRAM Through Hydride-Oxidation on Indium Tin Oxide Electrode by Supercritical CO ₂ Fluid. <i>IEEE Electron Device Letters</i> , 2015 , 36, 558-560	4.4	24
389	Resistive Switching Mechanism of Oxygen-Rich Indium Tin Oxide Resistance Random Access Memory. <i>IEEE Electron Device Letters</i> , 2016 , 37, 408-411	4.4	24
388	High temperature-induced abnormal suppression of sub-threshold swing and on-current degradations under hot-carrier stress in a-InGaZnO thin film transistors. <i>Applied Physics Letters</i> , 2013 , 103, 012101	3.4	23
387	On the Origin of Hole Valence Band Injection on GIFBE in PD SOI n-MOSFETs. <i>IEEE Electron Device Letters</i> , 2010 , 31, 540-542	4.4	23
386	A low temperature fabrication of HfO ₂ films with supercritical CO ₂ fluid treatment. <i>Journal of Applied Physics</i> , 2008 , 103, 074108	2.5	23
385	Improving Performance by Doping Gadolinium Into the Indium-Tin Oxide Electrode in HfO ₂ -Based Resistive Random Access Memory. <i>IEEE Electron Device Letters</i> , 2016 , 37, 584-587	4.4	23
384	Resistance Switching Characteristics Induced by O Plasma Treatment of an Indium Tin Oxide Film for Use as an Insulator in Resistive Random Access Memory. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 3149-3155	9.5	22
383	Enhanced electrical behavior from the galvanic effect in Ag-Cu alloy electrode conductive bridging resistive switching memory. <i>Applied Physics Letters</i> , 2018 , 113, 053501	3.4	22
382	Tri-Resistive Switching Behavior of Hydrogen Induced Resistance Random Access Memory. <i>IEEE Electron Device Letters</i> , 2014 , 35, 217-219	4.4	22
381	Solution-based Ediketone silver ink for direct printing of highly conductive features on a flexible substrate. <i>Journal of Materials Chemistry C</i> , 2013 , 1, 5161	7.1	22
380	The effect of high/low permittivity in bilayer HfO ₂ /BN resistance random access memory. <i>Applied Physics Letters</i> , 2013 , 102, 203507	3.4	22

379	Effects of channel width on electrical characteristics of polysilicon TFTs with multiple nanowire channels. <i>IEEE Transactions on Electron Devices</i> , 2005 , 52, 2343-2346	2.9	22
378	H ₂ O adsorption on amorphous In-Ga-Zn-O thin-film transistors under negative bias stress. <i>Applied Physics Letters</i> , 2017 , 111, 073506	3.4	21
377	Influence of Oxygen Concentration on Resistance Switching Characteristics of Gallium Oxide. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1387-1389	4.4	21
376	Systematic Investigations on Self-Heating-Effect-Induced Degradation Behavior in a-InGaZnO Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 3389-3395	2.9	21
375	Impact of static and dynamic stress on threshold voltage instability in high-k/metal gate n-channel metal-oxide-semiconductor field-effect transistors. <i>Applied Physics Letters</i> , 2011 , 98, 092112	3.4	21
374	Adaptive Synaptic Memory via Lithium Ion Modulation in RRAM Devices. <i>Small</i> , 2020 , 16, e2003964	11	21
373	Role of H ₂ O Molecules in Passivation Layer of a-InGaZnO Thin Film Transistors. <i>IEEE Electron Device Letters</i> , 2017 , 38, 469-472	4.4	20
372	. <i>IEEE Electron Device Letters</i> , 2020 , 41, 353-356	4.4	20
371	High-stability oxygen sensor based on amorphous zinc tin oxide thin film transistor. <i>Applied Physics Letters</i> , 2012 , 100, 262908	3.4	20
370	Investigating the improvement of resistive switching trends after post-forming negative bias stress treatment. <i>Applied Physics Letters</i> , 2011 , 99, 132104	3.4	20
369	Low temperature improvement method on characteristics of Ba(Zr _{0.1} Ti _{0.9})O ₃ thin films deposited on indium tin oxide/glass substrates. <i>Applied Physics A: Materials Science and Processing</i> , 2010 , 99, 291-295	2.6	20
368	Low-Temperature Passivation of Amorphous-Silicon Thin-Film Transistors With Supercritical Fluids. <i>IEEE Electron Device Letters</i> , 2007 , 28, 584-586	4.4	20
367	Analog Resistive Switching and Synaptic Functions in WO _x /TaO _x Bilayer through Redox-Induced Trap-Controlled Conduction. <i>ACS Applied Electronic Materials</i> , 2019 , 1, 2422-2430	4	19
366	Surface states related the bias stability of amorphous InGaZnO thin film transistors under different ambient gasses. <i>Thin Solid Films</i> , 2011 , 520, 1432-1436	2.2	19
365	Application of in-cell touch sensor using photo-leakage current in dual gate a-InGaZnO thin-film transistors. <i>Applied Physics Letters</i> , 2012 , 101, 212104	3.4	19
364	Physical and electrical characteristics of Ba(Zr _{0.1} Ti _{0.9})O ₃ thin films under oxygen plasma treatment for applications in nonvolatile memory devices. <i>Applied Physics A: Materials Science and Processing</i> , 2007 , 90, 329-331	2.6	19
363	Dynamic conductance characteristics in HfO _x -based resistive random access memory. <i>RSC Advances</i> , 2017 , 7, 12984-12989	3.7	18
362	Mechanism of Triple Ions Effect in GeSO Resistance Random Access Memory. <i>IEEE Electron Device Letters</i> , 2015 , 36, 552-554	4.4	18

361	. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 895-901	2.9	18
360	A Method to Reduce Forming Voltage Without Degrading Device Performance in Hafnium Oxide-Based 1T1R Resistive Random Access Memory. <i>IEEE Journal of the Electron Devices Society</i> , 2018 , 6, 341-345	2.3	18
359	On the Origin of Gate-Induced Floating-Body Effect in PD SOI p-MOSFETs. <i>IEEE Electron Device Letters</i> , 2011 , 32, 847-849	4.4	18
358	H ₂ O-Assisted O ₂ Adsorption in Sol-Gel Derived Amorphous Indium Gallium Zinc Oxide Thin Film Transistors. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H235		18
357	The asymmetrical degradation behavior on drain bias stress under illumination for InGaZnO thin film transistors. <i>Applied Physics Letters</i> , 2012 , 100, 222901	3.4	18
356	Charge storage characteristics of Mo nanocrystal dependence on Mo oxide reduction. <i>Applied Physics Letters</i> , 2008 , 93, 222101	3.4	18
355	Nonvolatile memory characteristics of nickel-silicon-nitride nanocrystal. <i>Applied Physics Letters</i> , 2007 , 91, 082103	3.4	18
354	Effects of plasma treatment time on surface characteristics of indium-tin-oxide film for resistive switching storage applications. <i>Applied Surface Science</i> , 2017 , 414, 224-229	6.7	17
353	. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1768-1771	4.4	17
352	Hopping conduction distance dependent activation energy characteristics of Zn:SiO ₂ resistance random access memory devices. <i>Applied Physics Letters</i> , 2013 , 102, 133503	3.4	17
351	Ultra-high resistive switching mechanism induced by oxygen ion accumulation on nitrogen-doped resistive random access memory. <i>Applied Physics Letters</i> , 2014 , 105, 223514	3.4	17
350	Impact of Mechanical Strain on GIFBE in PD SOI p-MOSFETs as Indicated From NBTI Degradation. <i>IEEE Electron Device Letters</i> , 2012 , 33, 303-305	4.4	17
349	Influence of molybdenum doping on the switching characteristic in silicon oxide-based resistive switching memory. <i>Applied Physics Letters</i> , 2013 , 102, 043508	3.4	17
348	Formation of Ge nanocrystals using Si _{1.33} Ge _{0.67} O ₂ and Si _{2.67} Ge _{1.33} N ₂ film for nonvolatile memory application. <i>Applied Physics Letters</i> , 2007 , 91, 102106	3.4	17
347	Abnormal hump in capacitance-voltage measurements induced by ultraviolet light in a-IGZO thin-film transistors. <i>Applied Physics Letters</i> , 2017 , 110, 023501	3.4	16
346	High performance of graphene oxide-doped silicon oxide-based resistance random access memory. <i>Nanoscale Research Letters</i> , 2013 , 8, 497	5	16
345	Carrier Transport and Multilevel Switching Mechanism for Chromium Oxide Resistive Random-Access Memory. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H103		16
344	Formation and nonvolatile memory characteristics of multilayer nickel-silicide NCs embedded in nitride layer. <i>Journal of Applied Physics</i> , 2008 , 104, 094303	2.5	16

343	Fabrication of one-transistor-capacitor structure of nonvolatile TFT ferroelectric RAM devices using Ba(Zr _{0.1} Ti _{0.9})O ₃ gated oxide film. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , 2007 , 54, 1726-30	3.2	16
342	. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2021 , 68, 264-274	3.9	16
341	Abnormal Dual Channel Formation Induced by Hydrogen Diffusion From SiNx Interlayer Dielectric in Top Gate a-InGaZnO Transistors. <i>IEEE Electron Device Letters</i> , 2017 , 38, 334-337	4.4	15
340	Reducing Forming Voltage by Applying Bipolar Incremental Step Pulse Programming in a 1T1R Structure Resistance Random Access Memory. <i>IEEE Electron Device Letters</i> , 2018 , 39, 815-818	4.4	15
339	Space electric field concentrated effect for Zr:SiO ₂ RRAM devices using porous SiO ₂ buffer layer. <i>Nanoscale Research Letters</i> , 2013 , 8, 523	5	15
338	Paraffin wax passivation layer improvements in electrical characteristics of bottom gate amorphous indiumgalliuminc oxide thin-film transistors. <i>Thin Solid Films</i> , 2011 , 520, 1608-1611	2.2	15
337	Role of germanium in the reduced temperature dependence of Ti-based nanocrystals formation for nonvolatile memory applications. <i>Applied Physics Letters</i> , 2009 , 95, 262110	3.4	15
336	Low-Temperature Synthesis of ZnO Nanotubes by Supercritical CO ₂ Fluid Treatment. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, K47		15
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